

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1662	"dielectric constant" with "3.9"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/28 11:06
S3	96	S1 and "gate insulator"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/22 11:50
S4	487	raised adj "source/drain"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/22 11:59
S5	66	S4 and "gate insulator"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/07 16:34
S6	0	S5 and "dielectric constant" with "3.9"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/07 16:31
S7	12	S5 and "dielectric constant"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/07 16:31
S8	1684	"dielectric constant" with "3.9"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/22 11:50
S9	99	S8 and "gate insulator"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/22 11:59
S10	45	S9 and @pd<"20030322"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/22 11:59
S11	406627	(("438") or ("257")).CLAS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/22 11:59

S12	6339	S11 and "gate insulator"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/22 11:59
S13	4154	S12 and @pd<"20030322"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/22 11:59
S14	30	S13 and (raised adj "source/drain")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/29 16:16
S15	114	S13 and "fermi level"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/22 12:05
S16	0	S15 and (raised adj "source/drain")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/22 12:05
S17	36	S15 and ("source/drain")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/22 12:05
S18	236	S13 and "work function"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/22 12:05
S19	32	S18 and "fermi level"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/22 12:05
S20	13	S19 and ("source/drain")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/22 12:06
S21	6	S18 and "dielectric constant" with "3.9"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/22 12:14

S22	3	S13 and "Hf film"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/22 12:24
S23	1	("6580137").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 08:23
S24	22	("4488162"   "5091324"   "5212104"   "5272432"   "5329138"   "5488237"   "5559368"   "5780899"   "5889410"   "6020239"   "6063699"   "6100123"   "6100146"   "6159807"   "6204532"   "6255171"   "6329256").PN. OR ("6580137").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/27 08:23
S25	1597	(257/410,407,411).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 14:30
S26	13	S25 and ((hafnium or hf) same TaN)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 14:33
S27	168	S25 and ((hafnium or hf) with ((hafnium adj oxide) or "hfo.sub. 2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 14:34
S28	42	S27 and (work adj function)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 14:35
S29	8	S28 and (fermi adj level)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 14:34
S30	406820	((438") or ("257")).CLAS:	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 14:42

S31	6346	S30 and "gate insulator"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 14:42
S32	4154	S31 and @pd<"20030322"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 14:42
S33	236	S32 and "work function"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 14:42
S34	32	S33 and "fermi level"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 14:42
S35	406820	(("438") or ("257")).CLAS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 14:58
S36	6346	S35 and "gate insulator"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 14:58
S37	4154	S36 and @pd<"20030322"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 14:58
S38	114	S37 and "fermi level"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 15:09
S39	388	"gate electrode" same "fermi level"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 15:10
S40	149	S39 and "work function"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 15:13

S41	97	("energy level" adj2 "band gap")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 15:16
S42	9	S41 and "work function"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 15:13
S43	1597	(257/410,407,411).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 15:34
S44	168	S43 and ((hafnium or hf) with ((hafnium adj oxide) or "hfo.sub. 2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 15:57
S45	320	"metal gate structure"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 15:58
S46	81	S45 and (hafnium or hf)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 15:58
S47	45	S46 and ((hafnium adj oxide) or ("hfo.sub.2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 15:58
S48	16	S47 and "TaN"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/27 15:58
S49	320	"metal gate structure"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/28 08:51
S50	81	S49 and (hafnium or hf)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/28 08:51
S51	0	("2004/0183143").URPN.	USPAT	OR	OFF	2005/12/28 09:37

S52	1	("6737309").PN.	US-PGPUB; OR USPAT; USOCR; EPO; JPO; IBM_TDB	OFF	2005/12/28 09:37	
S53	4731	transistor and (gate same (hafnium hf or (hafnium adj oxide) or ("hfo. sub.2")))	US-PGPUB; OR USPAT; USOCR; EPO; JPO; IBM_TDB	OFF	2005/12/28 11:07	
S54	517	S53 and (work adj function)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/28 11:30
S55	341	S54 and (fermi level)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/28 11:09
S56	147	S55 and @pd<"20040322"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/28 11:09
S57	74	S54 and (fermi adj level)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/28 11:09
S58	22	S57 and @pd<"20040322"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/28 11:09
S59	286	S54 and ("Ni" or "Ir" or "ZrO.sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/28 11:32
S60	10	("5189504"   "5965911"   "6140688"   "6184083"   "6270944"   "6271573"   "6376888"   "6482660").PN. OR ("6737309"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/28 14:02
S61	34	("energy level" with "band gap" with silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/28 15:40

S62	14	"fermi level" with (hafnium or hf)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/29 08:47
S63	28	("4743953"   "5668024"   "5940699"   "6140688"   "6184083"   "6278164").PN. OR ("6376888"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 10:47
S64	15	"first metal layer" adj ((hafnium or hf) or Ni or Ir)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 10:53
S65	45151	mosfet	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 10:53
S66	15	S64 and ("first metal layer" adj ((hafnium or hf) or Ni or Ir))	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 10:57
S67	4	S64 and ("first metal layer" adj (hafnium or hf))	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 10:58
S68	4	("first metal layer" adj (hafnium or hf))	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 14:05
S69	11	("first metal layer" adj (Ni or Ir))	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 11:00
S70	19250	"gate structure"	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 14:16
S71	557	S70 and ((first or second or third) adj "metal layer")	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 14:09
S72	160	S71 and ((hafnium or hf) or Ni or Ir)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 14:02
S73	6314	((257/407,412,903) or (438/592,300,197,199,299)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/29 14:04
S74	1809	S73 and mosfet	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/29 14:05
S75	1	S74 and ("first metal layer" adj (hafnium or hf))	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 14:16

S76	1	S74 and ("first metal layer" adj (Ni or Ir))	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 14:07
S77	66	S74 and ((first or second or third) adj "metal layer")	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 14:09
S78	28	S77 and (hf or TaN or "hfo.sub.2" or Ni or Ir)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 14:10
S79	1535	S73 and "gate structure"	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 14:16
S80	1	S79 and ("first metal layer" adj (hafnium or hf))	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 14:16
S81	28	("4743953"   "5668024"   "5940699"   "6140688"   "6184083"   "6278164").PN. OR ("6376888").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 14:17
S82	18	("4841346"   "5094966"   "5548143"   "5698884"   "5952701"   "6229188").PN. OR ("6541829").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 14:18
S83	10	("5189504"   "5965911"   "6140688"   "6184083"   "6270944"   "6271573"   "6376888"   "6482660").PN. OR ("6737309").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 14:19
S84	15	("5571734"   "5712208"   "5834353"   "5876788"   "5963810"   "6020243"   "6057584"   "6130164"   "6261887"   "6274905"   "6319730"   "6407435"   "6417546"   "6713846").PN. OR ("6784508").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/29 14:23
S85	500	(raised adj "source/drain")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/29 16:16
S86	24	S85 and "silicide region"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/29 16:18
S87	1678	"source/drain" adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/04 08:03

S88	500	raised adj "source/drain"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/03 08:00
S89	302	S88 and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/03 08:00
S90	224	S89 and silicide	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/03 08:01
S91	1678	"source/drain electrode"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/03 09:14
S92	4	raised with "source/drain electrode"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/03 08:44
S93	6	S91 and (hafnium or hf) with TaN	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/03 08:54
S94	168	S91 and (hafnium or hf)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/03 09:14
S95	67	"source/drain electrode layer"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/03 09:18
S96	11	S95 and (hafnium or hf)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/03 09:14
S97	500	raised adj "source/drain"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/04 08:03

S99	1678	"source/drain" adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/04 08:04
S10 0	1246	S99 and (Al or aluminum)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/04 08:04
S10 1	930494	"5" and raised	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/04 08:04
S10 2	152	S100 and raised	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/04 08:04
S10 3	500	raised adj "source/drain"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/04 09:31
S10 4	500	raised adj "source/drain"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/04 13:24
S10 5	383	S104 and (Al or aluminum)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/04 13:24
S10 6	1678	"source/drain electrode"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/04 15:05
S10 7	1285	"silicon layer" adj4 "insulator"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/04 15:05
S10 8	705	"silicon layer" adj2 "insulator"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/04 15:05

S10 9	259	"silicon layer" adj1 "insulator"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/04 15:24
S11 0	5088	"silicon region"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/04 15:23
S11 1	24	S110 and "silicon layer" adj1 "insulator"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/04 15:36
S11 2	74	S110 and "silicon layer" adj2 "insulator"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/04 15:36